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(54) Title: PREPARING A SURFACE OF A SAPPHIRE SUBSTRATE FOR FABRICATING HETEROSTRUCTURES

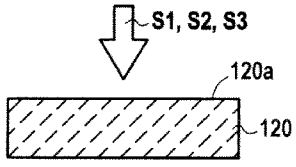


FIG.3A

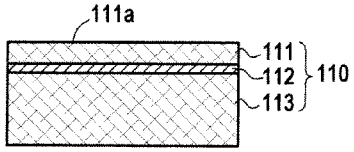


FIG.3B

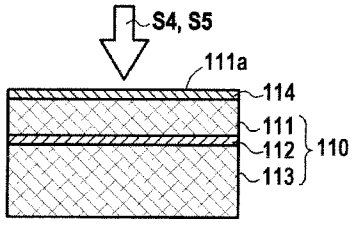


FIG.3C

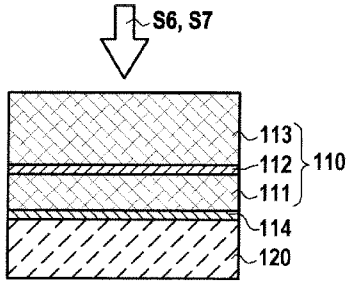


FIG.3D

(57) Abstract: The invention relates to a method of fabricating a heterostructure comprising at least a first substrate (120) made of sapphire and a second substrate (110) made of a material having a coefficient of thermal expansion that is different from that of the first substrate, the method including a step (S6) of molecular bonding the second substrate (110) on the first substrate (120) made of sapphire. In accordance with the invention, the method includes, prior to bonding the two substrates together, a step (S1) of stoving the first substrate (120) at a temperature that lies in the range 100°C to 500°C.

WO 2010/057842 A1

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